

Midterm Exam, Fall 2007, Solutions
 ECSE-6920 – Physical Foundations of Solid-State Devices

- Note:** (i) Put your name on paper, show your work, underline results, and always show units.
 (ii) Textbook, manuscript, excerpts, and calculators are allowed.

1. Assume that a one-dimensional wave function is given by

$$\psi = A \left(\frac{3}{16} - \frac{x^2}{L^2} + \frac{x^4}{L^4} \right) \quad \text{for} \quad -L/2 \leq x \leq L/2$$

$$\psi = 0 \quad \text{for} \quad x < -L/2 \quad \text{and} \quad x > L/2$$

- (a) Schematically sketch the wave function. Explain the purpose of the constant A .
 (b) Are ψ and ψ' continuous?
 (c) What is $\psi(x=0)$?
 (d) What is $\psi(x=L/2)$?
 (e) For $A = 1 / (L^{1/2})$, is the wave function normalized? Give **yes** or **no** answer and explain.
 (f) Calculate the position expectation value.
 (g) Assume that the potential energy surrounding the wave function is given by

$$U = 0 \quad \text{for} \quad -L/2 \leq x \leq L/2$$

$$U = +U_0 \quad \text{for} \quad x < -L/2 \quad \text{and} \quad x > L/2$$

What is the expectation value of the potential energy?

- (h) Is the expectation value of the total energy zero or non-zero? (Explain)

Solution:

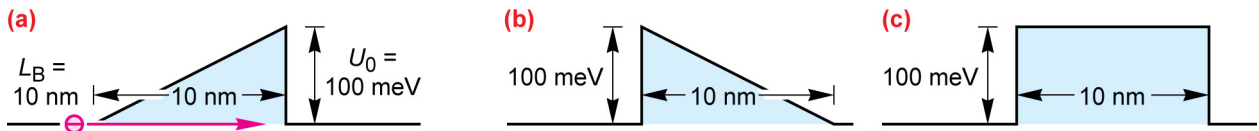
- (a) A is the normalization constant. The value of constant A is chosen such that the wave function is normalized, i.e. the integral of (or the area under) the probability density function of the particle is 1.
 (b) ψ is continuous. However, ψ' is not continuous.
 (c) $\psi(x=0) = \frac{3}{16}A$.
 (d) $\psi(x=L/2) = 0$.
 (e) For $A = 1 / (L^{1/2})$, the wave function is **not** normalized. The probability density function of the particle has its maxima at $x = 0$ where its value is $\left(\frac{3}{16}A\right)^2$. It is easily seen that the area under the probability function, which has to be equal to 1 for normalized wave function, is less than the area enclosed by rectangle with width = L and height = $\left(\frac{3}{16}A\right)^2$. For $A = 1 / (L^{1/2})$, the area of such a rectangle is $\frac{9}{256} \ll 1$.
 (f) The position expectation value, $\langle x \rangle = \int_{-\infty}^{\infty} \psi^*(x) x \psi(x) dx$. The given wave function is an even function. Therefore, $\langle x \rangle = \int_{-\infty}^{\infty} \text{even} \times \text{odd} \times \text{even} dx = \int_{-\infty}^{\infty} \text{odd} dx = 0$.
 (g) The expectation value of the potential energy $\langle U \rangle = \int_{-\infty}^{\infty} \psi^*(x) U(x) \psi(x) dx$. For the potential energy, $\langle U \rangle = \int_{-\infty}^{-L/2} \psi^*(x) U(x) \psi(x) dx + \int_{-L/2}^{+L/2} \psi^*(x) U(x) \psi(x) dx + \int_{+L/2}^{\infty} \psi^*(x) U(x) \psi(x) dx$. Therefore, $\langle U \rangle = 0$.

(h) The expectation value of the total energy, $\langle E \rangle = \langle E_{kin} \rangle + \langle E_{pot} \rangle = \langle E_{pot} \rangle$.

$$\langle E_{kin} \rangle = \int_{-\infty}^{\infty} \psi^*(x) \left(\frac{-\hbar^2}{2m} \frac{d^2}{dx^2} \right) \psi(x) dx.$$

Second derivative of an even function is an even function. Therefore, $\langle E_{kin} \rangle = \int_{-\infty}^{\infty} \text{even} \times \text{even} dx = \text{non-zero}$. Therefore, the expectation value of total energy, $\langle E \rangle$, is non-zero.

2. An electron with effective mass $m^* = 0.5 m_0$ tunnels through a barrier, shown in **Figure (a)** below that is triangular in shape with $U_0 = 100 \text{ meV}$ high and $L_B = 100 \text{ \AA} = 10 \text{ nm}$ wide.



- Give a formula for the tunneling barrier potential as a function of x .
- What is the tunneling probability of the electron calculated by using the WKB approximation?
- If a free electron with mass m_0 were to tunnel through the barrier, what would be its tunnel probability?
- Is the tunneling probability of the barrier shown in **Figure (b)** the same as the one shown in **Figure (a)**? If not, is it higher or lower?
- Is the tunneling probability of the barrier shown in **Figure (c)** the same as the one shown in **Figure (a)**? If not, is it higher or lower?

Solution:

(a) The formula for the tunneling barrier potential as a function of x .

- $U_0 = 10 \left(\frac{\text{meV}}{\text{nm}} \right) x$ for $0 \leq x \leq 10 \text{ nm}$
- $U_0 = 0$ for $x < 0$ and $x > 10 \text{ nm}$

(b) The tunneling probability of the electron calculated by using the WKB approximation is

$$T_{m^*} = e^{-\int_{x=0}^{L_B} 2\hbar^{-1} \sqrt{2m^*[U(x)-E]} dx} = e^{-15.33} = 2.2 \times 10^{-7}$$

(c) The tunnel probability a free electron with mass m_0 is

$$T_{m_0} = e^{-21.68} = 3.8 \times 10^{-10}$$

- The tunneling probability of the barrier shown in **Figure (b)** is the **same** as the one shown in **Figure (a)**.
- The tunneling probability of the barrier shown in **Figure (c)** is **lower** than the one shown in **Figure (a)**.

3. Given are the dispersion relations (energy band structures) of (a) gallium arsenide and (b) silicon.
- Identify a direct and an indirect band-gap semiconductor material. (Explain)
 - Which material has a smaller conduction-band electron effective mass, Si or GaAs?
 - Can an effective mass become negative? (Explain)
 - If so, show one region in the E -versus- k diagram, in which the electron effective mass is negative? (Mark location in figure)
 - Highlight the range of k values in the figure for which the materials have an electron effective mass and hole effective mass that can be assumed to be a constant.
 - A dispersion relation is given by $E = \alpha k^2$, where $\alpha = 5 \times 10^{-39} \text{ J m}^2$. Calculate the numerical value of the effective mass.
 - For $E = 100 \text{ meV}$, calculate the particle velocity.
 - For $E = 100 \text{ meV}$, calculate wave number k .
 - For $E = 100 \text{ meV}$, calculate the wavelength λ .
 - If the above E is purely kinetic, calculate the group velocity.

Solution:

- GaAs is direct band-gap and Si is indirect band-gap material. The conduction-band minimum of GaAs occurs directly above the valence-band maximum, i.e. along the same direction in k -space, allowing a direct transition of electron from conduction-band to valence-band, without any change in momentum. Such a transition is not possible in Si as the conduction-band minimum and the valence-band maximum occur in different direction in k -space.
- GaAs has smaller conduction-band electron effective mass.
- Yes. Effective mass is proportional to the curvature of the band structure. Therefore, the effective mass takes a negative value where the slope of the band structure decreases with increasing value of $|k|$.
- See figure. The red ellipses indicate the region in the E -versus- k diagram, in which the electron effective mass is negative.
- See figure. The yellow highlights indicate the range of k values in the figure for which the materials have an electron effective mass and hole effective mass that can be assumed to be a constant, because the dispersion relation in these regions can be approximated with a parabola.
- Effective mass $m^* = 1.11 \times 10^{-30} \text{ kg}$.
- The particle velocity is given by,

$$v = \sqrt{\frac{2E}{m^*}} = \sqrt{\frac{2 \times 100 \times 10^{-3} \text{ eV} \times 1.602 \times 10^{-19} \text{ C}}{1.11 \times 10^{-30} \text{ kg}}} = 1.7 \times 10^5 \frac{\text{m}}{\text{s}}$$

- The wavenumber k is given by,

$$k = \frac{\sqrt{2m^*E}}{\hbar} = \frac{\sqrt{2 \times 1.11 \times 10^{-30} \text{ kg} \times 100 \times 10^{-3} \text{ eV} \times 1.602 \times 10^{-19} \text{ C}}}{1.05 \times 10^{-34} \text{ kg.m}^2.\text{s}^{-1}}$$

$$= 1.8 \times 10^9 \text{ m}^{-1}$$

- The wavelength of the particle $\lambda = \frac{2\pi}{k} = \frac{2 \times 3.14}{1.8 \times 10^9 \text{ m}^{-1}} = 3.5 \times 10^{-9} \text{ m}$.

- The group velocity $v_{gr} = \frac{d\omega}{dk}$. For the given particle, $E = \frac{\hbar^2 k^2}{2m^*} = \hbar\omega$. Therefore, $\omega = \frac{\hbar k^2}{2m^*}$.

$$\text{Thus, } v_{gr} = \frac{d}{dk} \left(\frac{\hbar k^2}{2m^*} \right) = \frac{\hbar k}{m^*} = \frac{1.05 \times 10^{-34} \text{ kg m}^2 \text{ s}^{-1} \times 1.8 \times 10^9 \text{ m}^{-1}}{1.11 \times 10^{-30} \text{ kg}} = 1.7 \times 10^5 \frac{\text{m}}{\text{s}}$$

